

IN THE CLAIMS:

Please amend claims 6, 12, 18, 24 and 30 as follows:

*Sub D<sup>2</sup> A<sup>1</sup>*  
6. (Amended) The device of claim 1 wherein said display is a digital  
gradation display.

*Sub D<sup>4</sup> A<sup>2</sup>*  
12. (Amended) The device of claim 7 wherein said display is a digital  
gradation display.

*Sub D<sup>4</sup> A<sup>3</sup>*  
18. (Amended) The device of claim 13 wherein said display is a digital  
gradation display.

*Sub D<sup>5</sup> A<sup>4</sup>*  
24. (Amended) The device of claim 19 wherein said display is a digital  
gradation display.

*Sub D<sup>10</sup> A<sup>5</sup>*  
30. (Amended) The device of claim 25 wherein said display is a digital  
gradation display.

Please add new claims 31-55 as follows:

*Sub D<sup>11</sup> A<sup>6</sup>*  
--31. The device of claim 1 wherein said display further comprises a tuner  
for receiving television radio wave to constitute a television.

32. The device of claim 7 wherein said display further comprises a tuner  
for receiving television radio wave to constitute a television.

33. The device of claim 13 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

34. The device of claim 19 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

35. The device of claim 25 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

36. The device of claim 31 wherein said television is a liquid crystal television.

37. The device of claim 32 wherein said television is a liquid crystal television.

38. The device of claim 33 wherein said television is a liquid crystal television.

39. The device of claim 34 wherein said television is a liquid crystal television.

40. The device of claim 35 wherein said television is a liquid crystal television.

41. The device of claim 1 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising

a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

42. The device of claim 7 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

43. The device of claim 13 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

44. The device of claim 19 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

45. The device of claim 25 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

46. The device of claim 1 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted

nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

47. The device of claim 7 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

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48. The device of claim 13 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

49. The device of claim 19 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

50. The device of claim 25 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.